30V N-Channel Enhancement Mode Power MOSFET

Description

EMR12N03TC uses advanced power trench technology that has been especially tailored to minimize the on-state resistance and yet maintain superior switching performance.

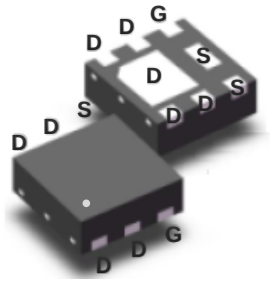
Features

- V_{DS}= 30V, I_D = 12A
  $R_{DS(on)}$ < 8.5mΩ @ V_{GS} = 10V
  $R_{DS(on)}$ < 12.5mΩ @ V_{GS} = 4.5V
- Green Device Available
- High Power and Current Handing Capability

Applications

- Battery Protection
- Power Management
- Load Switch

Schematic & PIN Configuration



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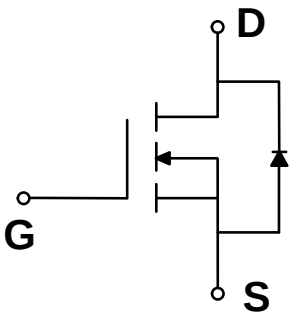

Absolute Maximum Ratings (T_A = 25°C, unless otherwise noted)

Parameter		Symbol	Value	Unit
Drain-Source Voltage		V_{DS}	30	V
Gate-Source Voltage		V_{GS}	±20	V
Continuous Drain Current	T_A=25°C	I_D	12	A
	T_A=100°C		7.6	
Pulsed Drain Current [1]		I_{DM}	48	A
Single Pulse Avalanche Energy [2]		EAS	45	mJ
Total Power Dissipation	T_A=25°C	P_D	2.2	W
Operating Junction and Storage Temperature Range		T_J ,T_{STG}	-55 to +150	°C

Thermal Characteristics

Parameter	Symbol	Value	Unit
Thermal Resistance from Junction to Ambient [3]	$R_{\theta JA}$	56.8	°C/W

Electrical Characteristics (T_J = 25°C, unless otherwise noted)

Parameter		Symbol	Test Conditions	Min	Typ	Max	Unit
Static Characteristics							
Drain-Source Breakdown Voltage		$V_{(BR)DSS}$	V_{GS} = 0V, I_D = 250μA	30	-	-	V
Gate-body Leakage Current		I_{GSS}	V_{DS} = 0V, V_{GS} = ±20V	-	-	±100	nA
Zero Gate Voltage Drain Current	T_J=25°C	I_{DSS}	V_{DS} = 30V, V_{GS} = 0V	-	-	1	μA
	T_J=100°C			-	-	100	
Gate Threshold Voltage		$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250μA	1.0	1.5	2.0	V
Drain-Source on-state Resistance (4)		$R_{DS(on)}$	V_{GS} = 10V, I_D = 8A	-	6.5	8.5	mΩ
			V_{GS} = 4.5V, I_D = 6A	-	9	12.5	
Dynamic Characteristics (5)							
Input Capacitance		C_{iss}	V_{DS} = 15V, V_{GS} = 0V, f = 1MHz	-	1285	-	pF
Output Capacitance		C_{oss}		-	170	-	
Reverse Transfer Capacitance		C_{rss}		-	133	-	
Gate Resistance		R_g	f =1MHz	-	2	-	Ω
Switching Characteristics (5)							
Total Gate Charge		Q_g	V_{GS} = 10V, V_{DS} = 15V, I_D= 8A	-	23.5	-	nC
Gate-Source Charge		Q_{gs}		-	4.3	-	
Gate-Drain Charge		Q_{gd}		-	3.4	-	
Turn-On Delay Time		$t_{d(on)}$	V_{GS} = 10V, V_{DD} = 15V, R_G = 3Ω, I_D= 8A	-	6.9	-	ns
Rise Time		t_r		-	2	-	
Turn-Off Delay Time		$t_{d(off)}$		-	22.3	-	
Fall Time		t_f		-	5.2	-	
Body Diode Reverse Recovery Time		t_{rr}	I_F=8A, dI/dt=100A/μs	-	17	-	ns
Body Diode Reverse Recovery Charge		Q_{rr}		-	2.7	-	nC
Drain-Source Body Diode Characteristics							
Diode Forward Voltage (4)		V_{SD}	I_S = 1A, V_{GS} = 0V	-	-	1.2	V
Continuous Source	T_A=25°C	I_S		-	-	12	A

Note1：Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}$=150°C

Note2：The test condition is V_{DD}=20V, V_{GS}=10V, L= 0.4mH, I_{AS}= 15A.

Note3：The data tested by surface mounted on a 1 inch2 FR-4 board with 2OZ copper, The value in any given application depends on the user's specific board design.

Note4：The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%.

Note5：This value is guaranteed by design hence it is not included in the production test.

Typical Characteristics

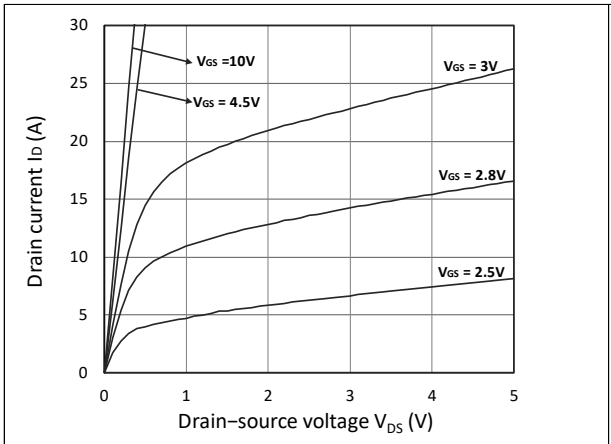

Figure 1. Output Characteristics

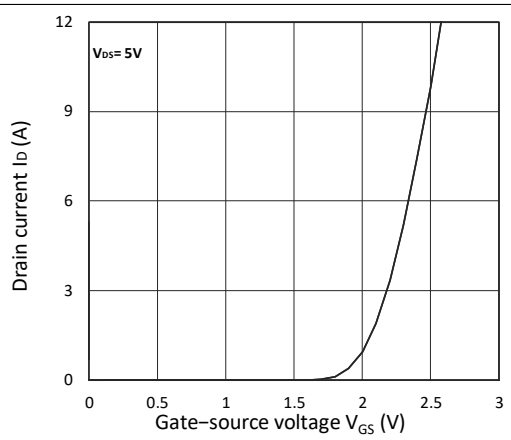

Figure 2. Transfer Characteristics

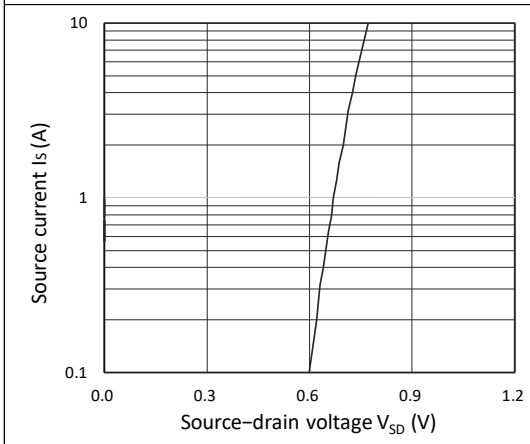

Figure 3. Forward Characteristics of Reverse

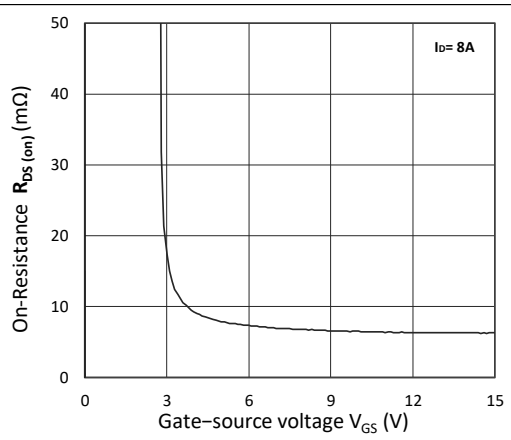

Figure 4. $R_{DS(ON)}$ vs. V_{GS}

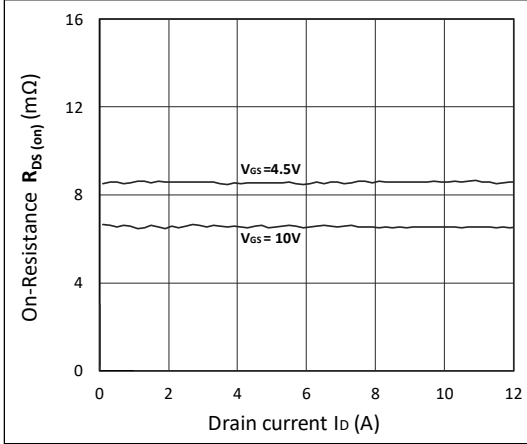

Figure 5. $R_{DS(ON)}$ vs. I_D

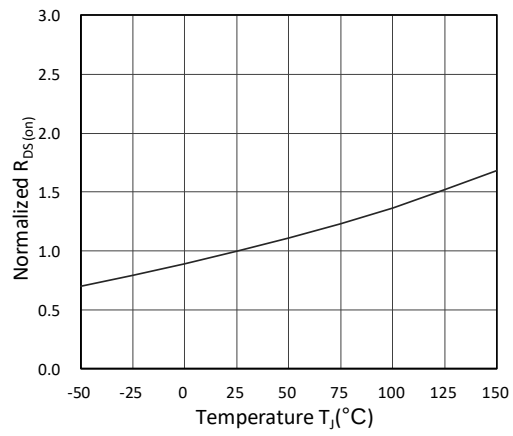

Figure 6. Normalized $R_{DS(on)}$ vs. Temperature

Typical Characteristics(Continued)

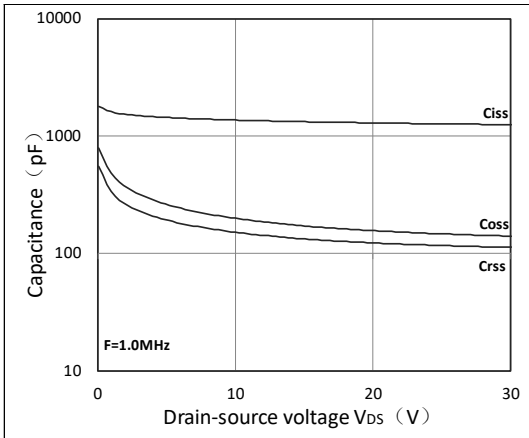

Figure 7. Capacitance Characteristics

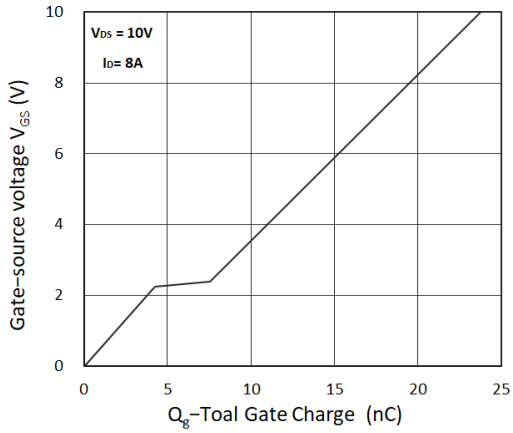

Figure 8. Gate Charge Characteristics

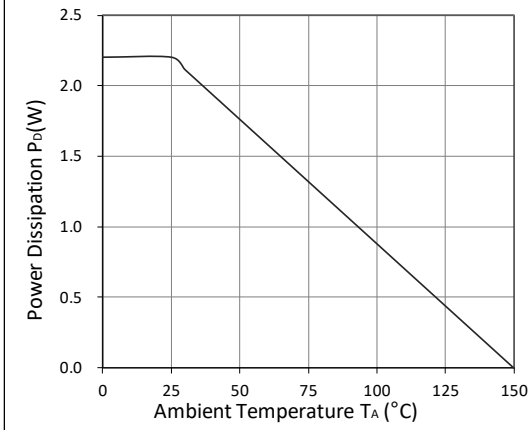

Figure 9. Power Dissipation

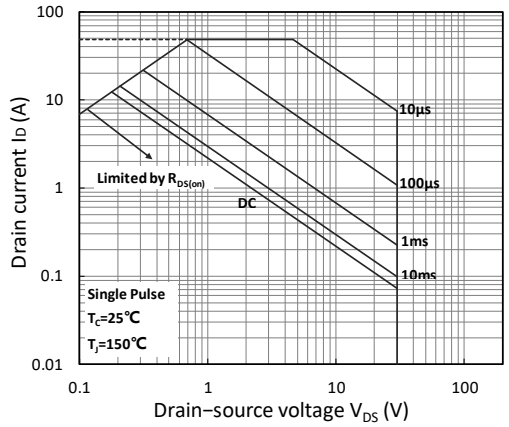

Figure10. Safe Operating Area

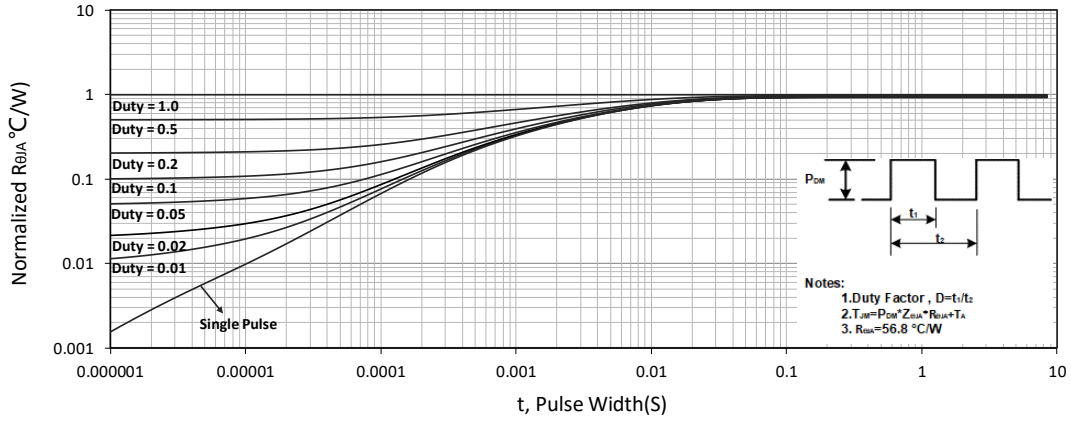

Figure 11. Normalized Maximum Transient Thermal Impedance

Test Circuit

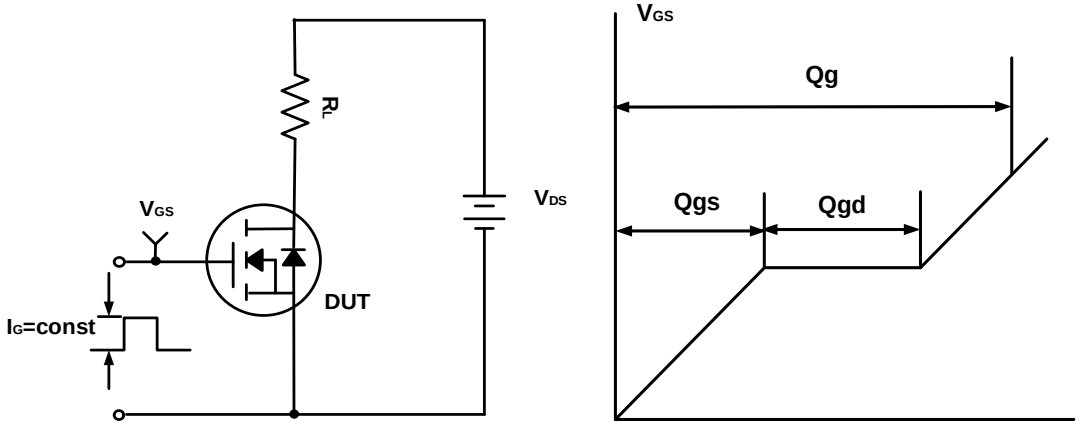

Figure A. Gate Charge Test Circuit & Waveforms

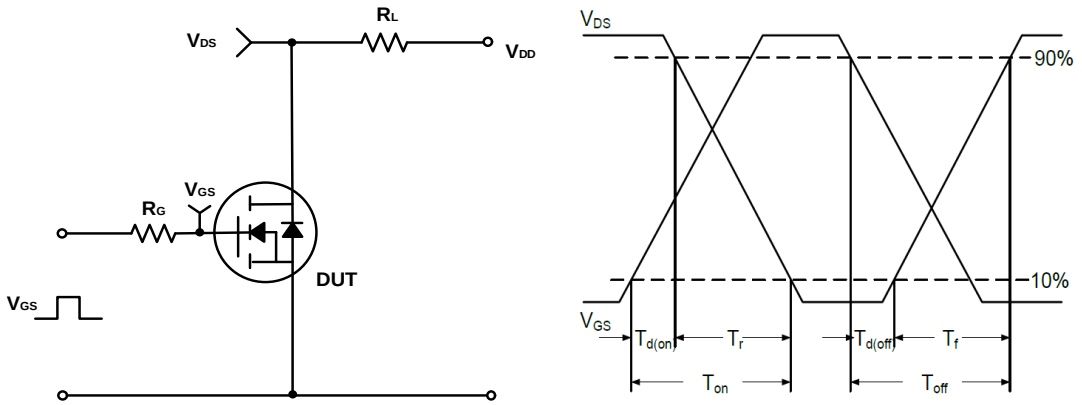

Figure B. Switching Test Circuit & Waveforms

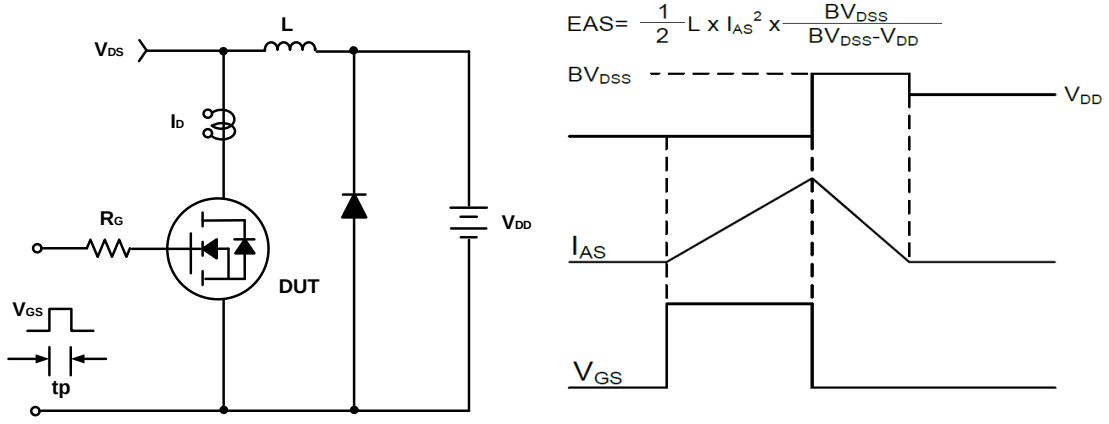

Figure C. Unclamped Inductive Switching Circuit & Waveforms

Package Dimension

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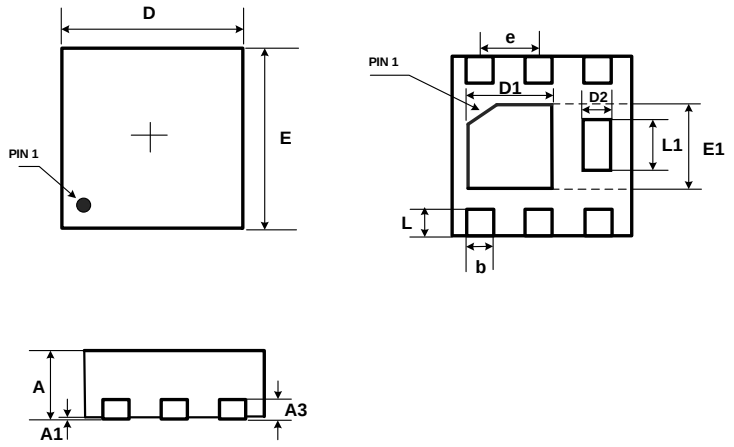


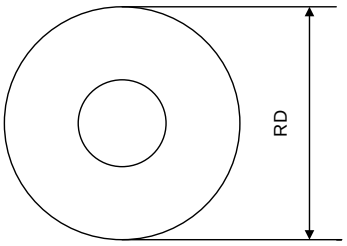
SYMBOL	MILLIMETER	
	MIN	MAX
A	0.50	0.60
A1	0.00	0.05
A3	0.152REF	
b	0.25	0.35
D	1.90	2.10
D1	0.80	1.00
E	1.90	2.10
E1	0.80	1.00
L1	0.46	0.66
e	0.65BSC	
D2	0.25	0.35
L	0.25	0.35

Ordering Information

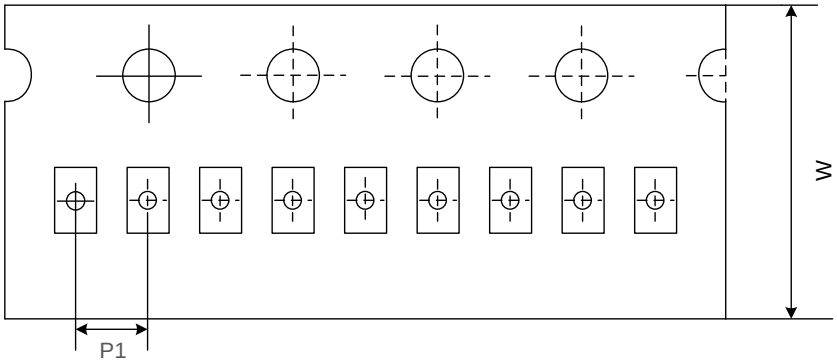
Part	Package	Marking	Packing method	MPQ
EMR12N03TC	DFN2020-6L	R12N03C	Tape and Reel	3K/Reel

Tape and Reel

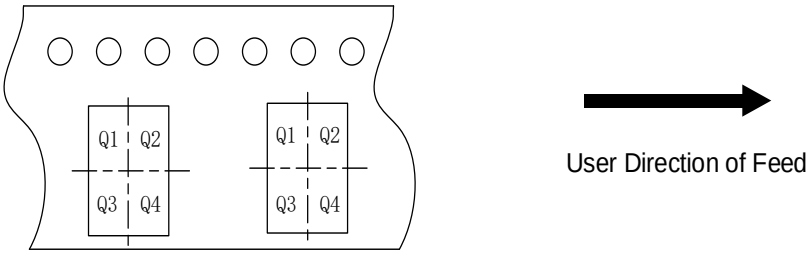
Reel Dimensions



Tape Dimensions



Quadrant Assignments For PIN1 Orientation In Tape



RD	Reel Dimensions	7 inch
W	Overall width of the carrier tape	8 mm
P1	Pitch between successive cavity centers	4mm
Pin1	Pin1 Quadrant	Q1

Revision History and Checking Table

Version	Date	Revision Item	Modifier	Function & Spec Checking	Package & Tape Checking
1.0	2023-08-16	Released Version	Chen Zu Xiong	Qi Shu Kun	Liu Jia Ying